



CPH6623 — P-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- 4V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-30	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		-1.5	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-6.0	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (900mm ² ×0.8mm) 1unit	0.9	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D =-1mA, V _{GS} =0V	-30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V			-1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	y _{fs}	V _{DS} =-10V, I _D =-0.8A	0.9	1.5		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =-0.8A, V _{GS} =-10V		210	275	mΩ
	R _{DS(on)2}	I _D =-0.4A, V _{GS} =-4V		350	490	mΩ
Input Capacitance	C _{iss}	V _{DS} =-10V, f=1MHz		185		pF
Output Capacitance	C _{oss}	V _{DS} =-10V, f=1MHz		30		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =-10V, f=1MHz		20		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		7		ns
Rise Time	t _r	See specified Test Circuit.		4		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit.		22		ns
Fall Time	t _f	See specified Test Circuit.		8		ns

Marking : WJ

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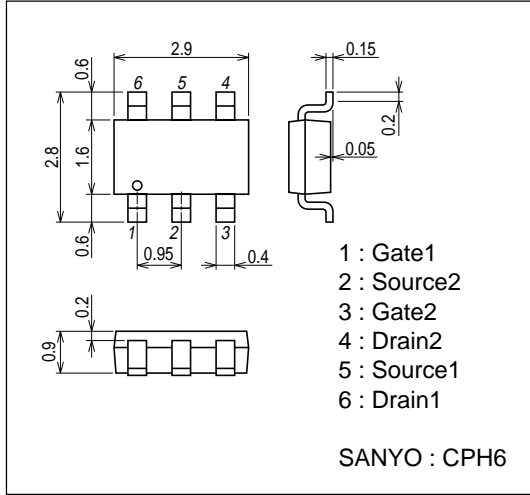
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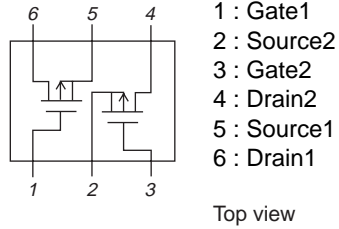
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	V _{DS} =-10V, V _{GS} =-10V, I _D =-1.5A		4.7		nC
Gate-to-Source Charge	Qgs	V _{DS} =-10V, V _{GS} =-10V, I _D =-1.5A		0.8		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =-10V, V _{GS} =-10V, I _D =-1.5A		0.7		nC
Diode Forward Voltage	V _{SD}	I _S =-1.5A, V _{GS} =0V		-0.88	-1.5	V

Package Dimensions

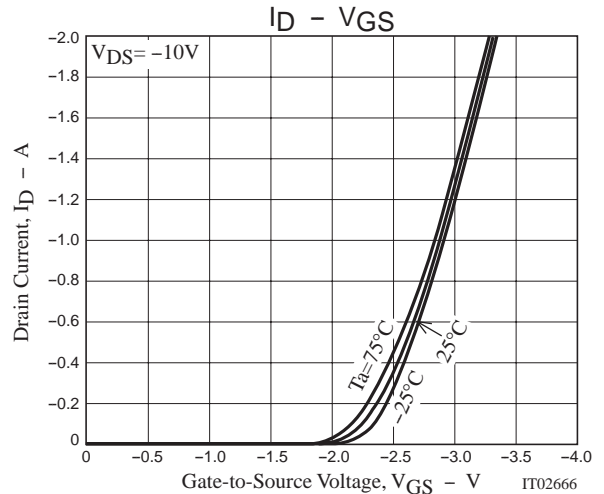
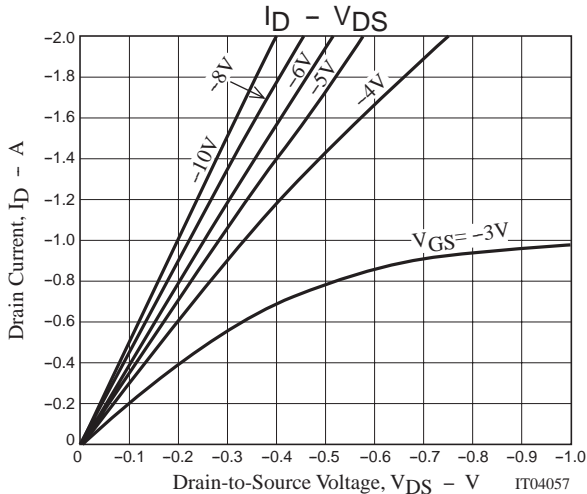
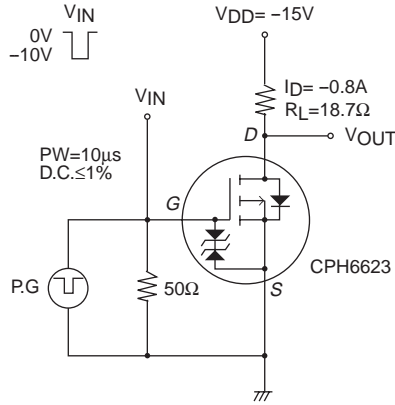
unit : mm
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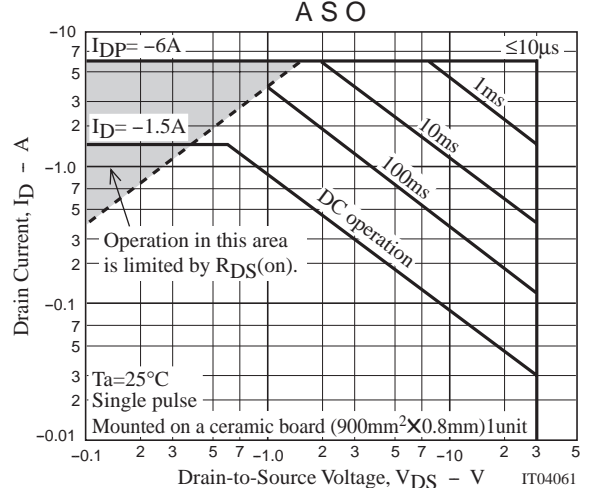
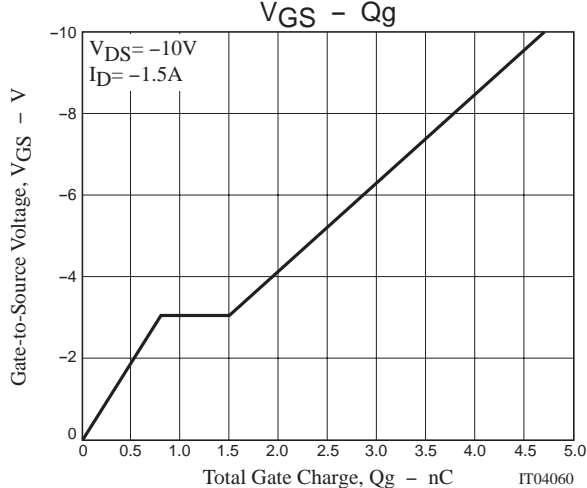
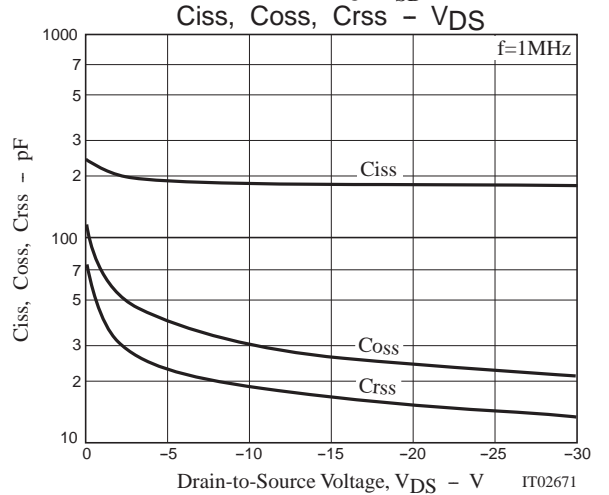
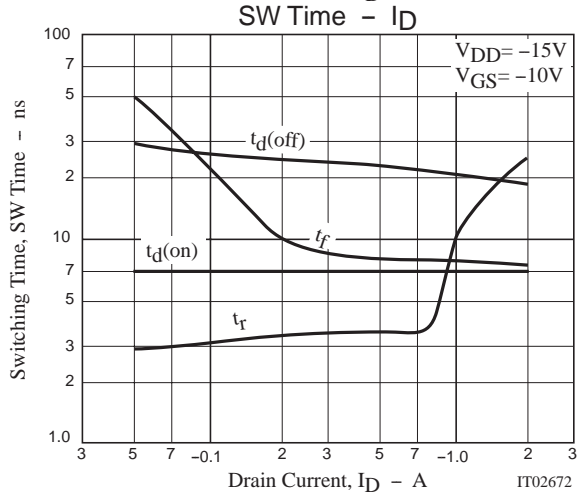
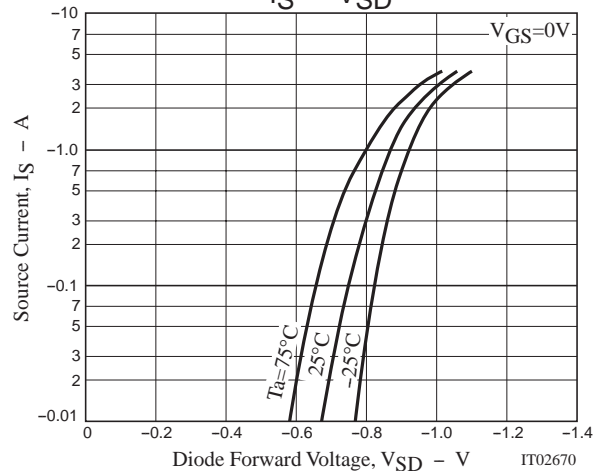
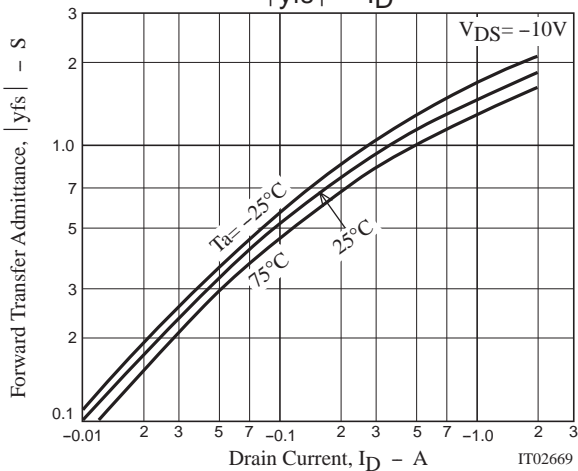
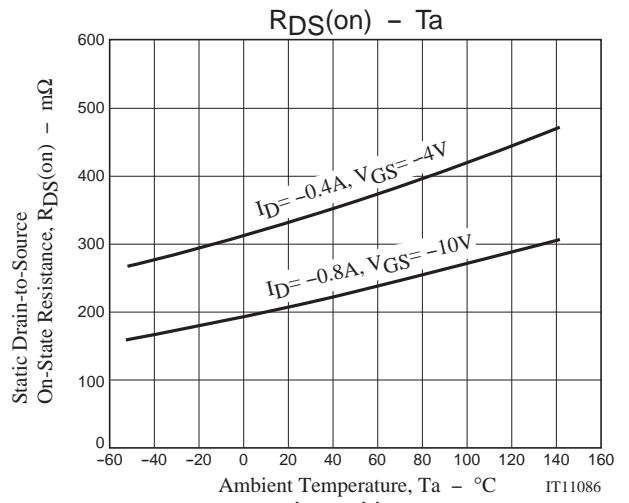
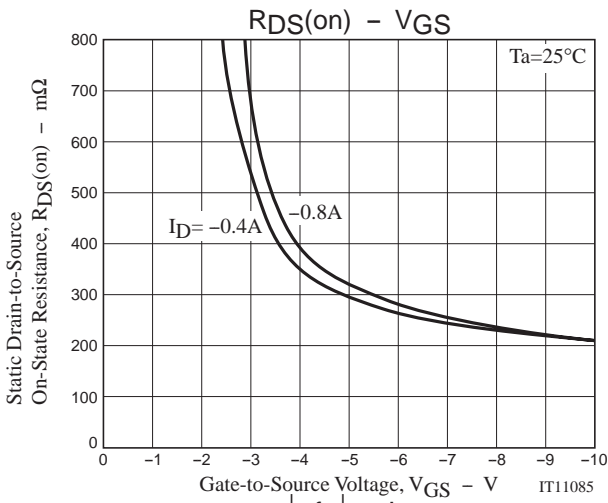
Electrical Connection

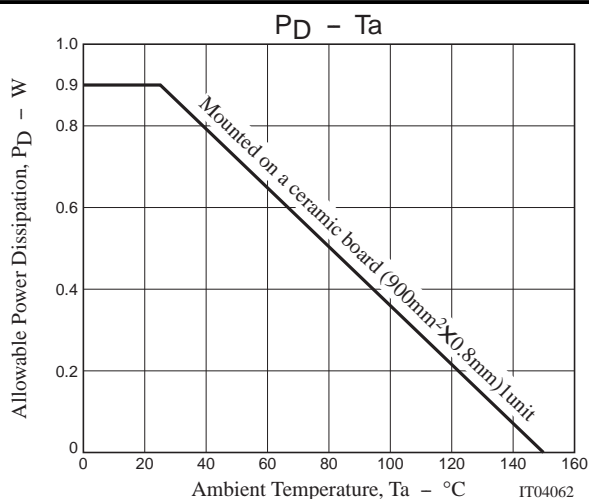


Switching Time Test Circuit



CPH6623





Note on usage : Since the CPH6623 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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